

Title (en)  
Read only storage matrix.

Title (de)  
Festwertspeichermatrix.

Title (fr)  
Matrice de mémoire morte.

Publication  
**EP 0041603 A1 19811216 (EN)**

Application  
**EP 81102886 A 19810415**

Priority  
US 15792180 A 19800609

Abstract (en)  
[origin: US4347585A] This matrix has high barrier Schottky diodes at Read or Reproduce Only Storage (ROS) matrix crossovers to represent 1's (the absence of diodes representing 0's) and low barrier Schottky diodes connected to select individual column lines (bit lines) of the ROS matrix. A current sink is connected to each column. Any unselected column causes the current in that column to be diverted through the respective low barrier diode, thus preventing that current from flowing into the selected word line. The only current that flows into the selected word line of a matrix depends from the single selected column current source.

IPC 1-7  
**G11C 17/06**

IPC 8 full level  
**G11C 17/06** (2006.01); **G11C 17/08** (2006.01)

CPC (source: EP US)  
**G11C 17/06** (2013.01 - EP US); **G11C 17/08** (2013.01 - EP US)

Citation (search report)

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EP0184138A3; US4935050A

Designated contracting state (EPC)  
DE FR GB

DOCDB simple family (publication)  
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DOCDB simple family (application)  
**EP 81102886 A 19810415; DE 3164678 T 19810415; JP 5067381 A 19810406; US 15792180 A 19800609**